



# **Phase Control Thyristor**

DS5817-3 January 2014 (LN31254)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR1950C52* DCR1950C50 DCR1950C48	5200 5000 4800	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 300\text{mA}, \\ V_{DRM}, V_{RRM}  t_p &= 10\text{ms}, \\ V_{DSM}  \&  V_{RSM} &= \\ V_{DRM}  \&  V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. \*5000V @ -40°C, 5200V @ 0°C

## **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

## DCR1950C52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

## **KEY PARAMETERS**

5200V
1950A
26250A
1500V/µs
300A/µs

## \* Higher dV/dt selections available

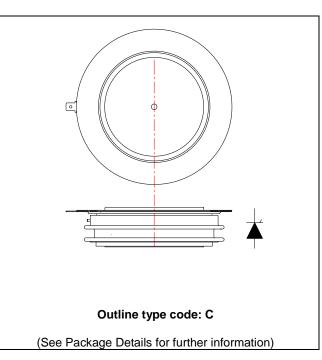


Fig. 1 Package outline





## **CURRENT RATINGS**

## $T_{\text{case}}$ = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	1950	А
I <sub>T(RMS)</sub>	RMS value	-	3060	А
I <sub>T</sub>	Continuous (direct) on-state current	-	3000	А

## **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, T <sub>case</sub> = 125°C	26.25	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	3.45	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	Min.	Max.	Units	
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.0101	°C/W
		Single side cooled	Anode DC	-	0.0176	°C/W
			Cathode DC	-	0.0239	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 37kN	Double side	-	0.0025	°C/W
		(with mounting compound)	Single side	-	0.005	°C/W
T <sub>vj</sub>	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
F <sub>m</sub>	Clamping force			33.0	41.0	kN





# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditio	Test Conditions		Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, ga	ate open	-	1500	V/µs
dI/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	150	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	300	A/µs
		$t_r < 0.5 \mu s, T_j = 125 ^{\circ} C$				
$V_{T(TO)}$	Threshold voltage – Low level	500A to 2000A at T <sub>case</sub> = 125	5°C	-	0.932	>
	Threshold voltage – High level	2000A to 7000A at T <sub>case</sub> = 12	25°C	-	1.100	٧
r <sub>T</sub>	On-state slope resistance – Low level	500A to 2000A at T <sub>case</sub> = 125°C		-	0.434	mΩ
	On-state slope resistance – High level	2000A to 7000A at T <sub>case</sub> = 125°C		-	0.346	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, $10\Omega$		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 1$ A/ $\mu$ s,		700	1100	μs
		dV <sub>DR</sub> /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 2000A$ , $T_j = 125$ °C, $dI/dt - 1A/\mu s$ ,		1200	2800	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I <sub>H</sub>	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 50$	0A, I <sub>T</sub> = 5A	-	300	mA



## **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	350	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	10	mA

## **CURVES**

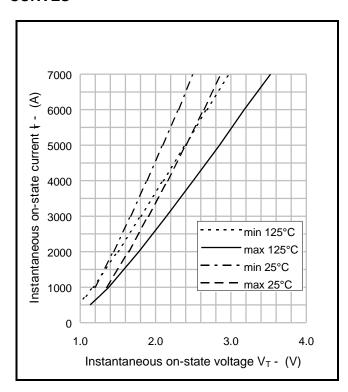


Fig.2 Maximum & minimum on-state characteristics

 $V_{TM}$  EQUATION

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = -0.142705

B = 0.203033

C = 0.000358

D = -0.00751

these values are valid for  $T_j = 125^{\circ}\text{C}$  for  $I_T 100\text{A}$  to 7200A



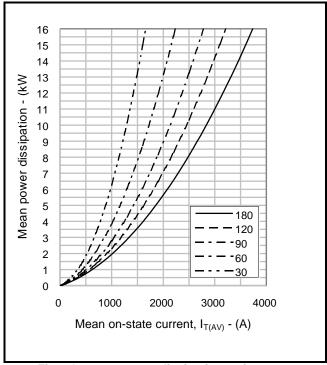


Fig.3 On-state power dissipation – sine wave

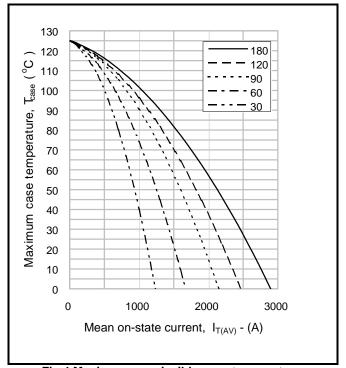


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

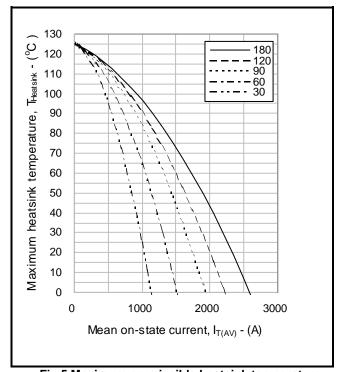


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

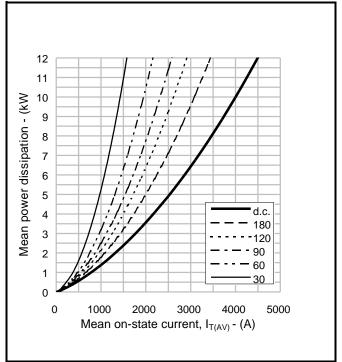


Fig.6 On-state power dissipation - rectangular wave



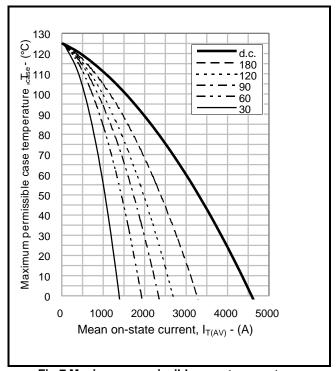


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

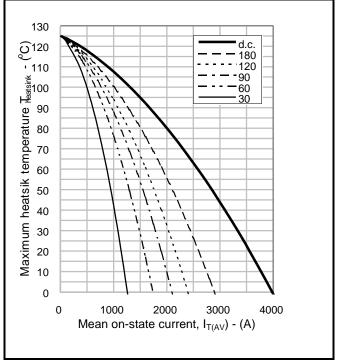
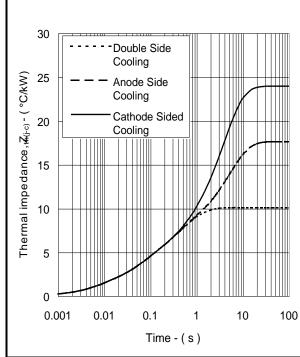


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R <sub>i</sub> (°C/kW)	1.1043	2.576	4.5096	1.9009
	T <sub>i</sub> (s)	0.006176	0.0517916	0.3820376	1.06
Anode side cooled	R <sub>i</sub> (°C/kW)	1.0977	2.4566	4.0469	9.9994
	T <sub>i</sub> (s)	0.006153	0.050142	0.3129407	5.27
Cathode side cooled	R <sub>i</sub> (°C/kW)	1.1519	2.8926	2.4064	17.4793
	T. (s)	0.006380	0.0582053	0.3775516	3 07

 $Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$  [1]

 $\Delta R_{\text{th(j-c)}}$  Conduction

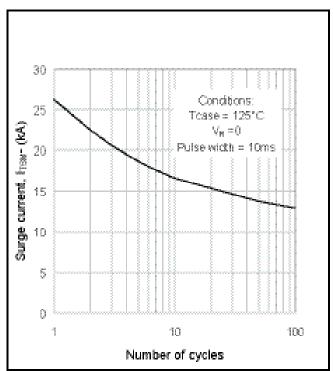
Tables show the increments of thermal resistance  $R_{\text{th(j-c)}}$  when the device operates at conduction angles other than d.c.

Double side cooling				Anode Side Cooling		
	$\Delta Z_{th}$ (	$\Delta Z_{th}(z)$			$\Delta Z_{i}$	<sub>h</sub> (z)
θ°	sine.	rect.		θ°	sine.	rect.
180	1.95	1.26		180	1.95	1.26
120	2.32	1.89		120	2.32	1.89
90	2.74	2.27		90	2.74	2.27
60	3.14	2.70		60	3.14	2.70
30	3.46	3.19		30	3.46	3.19
15	3.61	3 47	ĺ	15	3.62	3 47

Cathode Sided Cooling			
$\Delta Z_{th}$ (z)			
sine.	rect.		
1.95	1.26		
2.31	1.88		
2.72	2.26		
3.12	2.68		
3.43	3.17		
3.58	3.44		
	ΔZ <sub>tt</sub> sine. 1.95 2.31 2.72 3.12 3.43		

Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)





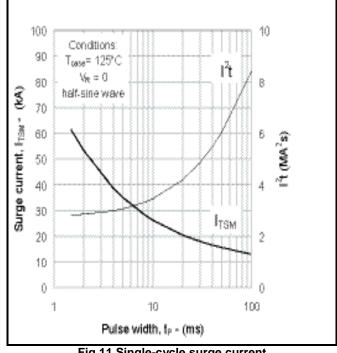
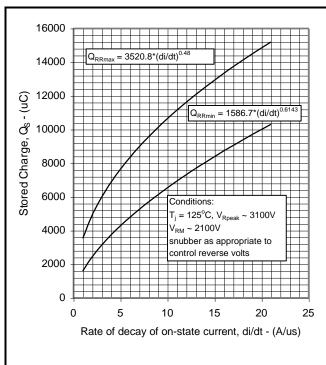


Fig.10 Multi-cycle surge current

Fig.11 Single-cycle surge current



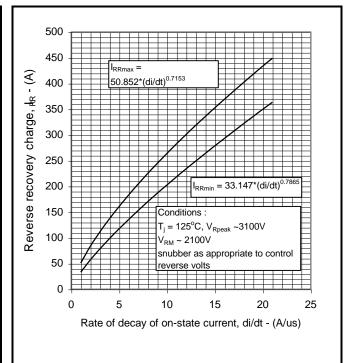


Fig.12 Stored Charge

Fig.13 Reverse recovery current

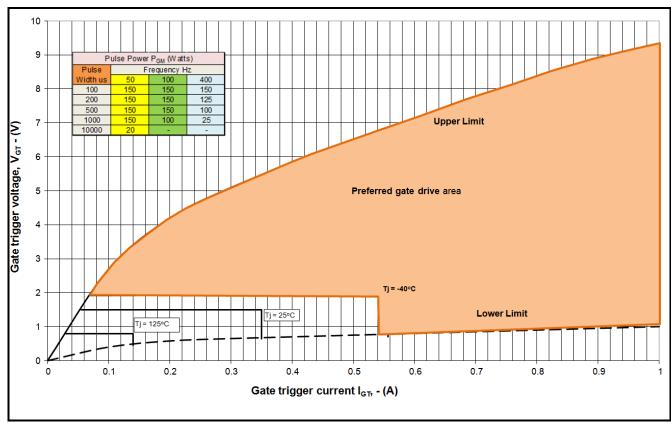


Fig14 Gate Characteristics

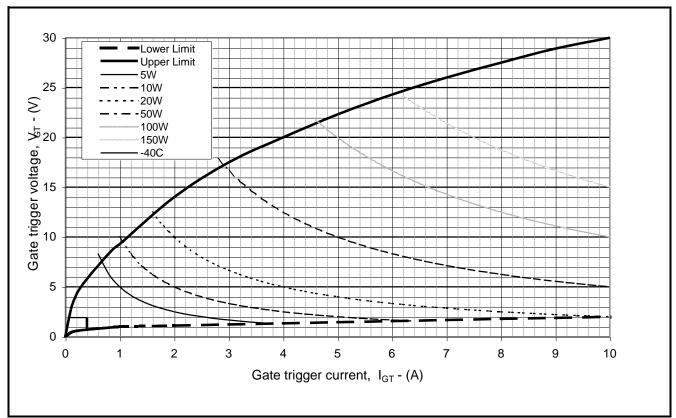


Fig. 15 Gate characteristics





### **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

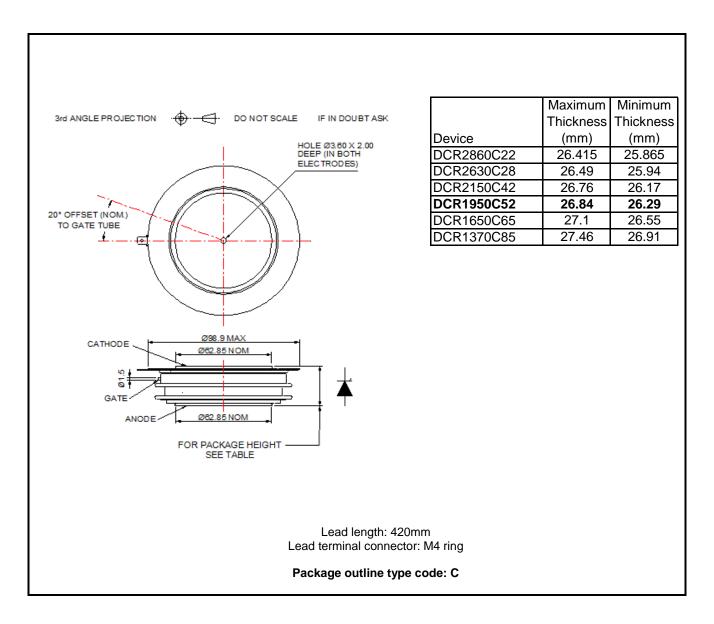


Fig.16 Package outline





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